

International Application No.: PCT/JP2004/015621
U.S. Patent Application No.: Unknown
May 24, 2006
Page 3 of 10

IN THE ABSTRACT:

Please replace the Abstract of the Disclosure originally filed with the above-identified patent application with the following new Abstract of the Disclosure:

ABSTRACT OF THE DISCLOSURE

A method for forming a thick film pattern forms a thick film pattern having a large thickness, a high hardness, and a high aspect ratio and exhibiting high dimension precision and high shape precision. In the method, a photosensitive paste including an inorganic powder, a photosensitive monomer, and a photopolymerization initiator and containing substantially no polymer is applied to a support so as to form a photosensitive paste film. The resulting photosensitive paste film is subjected to an exposure treatment and, thereafter, development is conducted so as to form a predetermined thick film pattern. Alternatively, a photolithography photosensitive paste including an inorganic powder, a photosensitive monomer, a photopolymerization initiator, and a polymer is used, wherein a ratio (weight ratio) of the photosensitive monomer to a total amount of the photosensitive monomer and the polymer is about 0.86 or more.